

Amendments to the Specification

Please replace paragraph [0055] of the Specification with the following paragraph:

R1 [0055] If fragments 202 and 204 are both being utilized for forming PMOS transistors, the layers ~~232~~ 230 and 236 can be identical to one another and formed in a common processing step; the layers 232 and 238 can be identical to one another and formed in the same processing step; and the layers 234 and 240 can be identical to one another and formed in the same processing step. Also, if layers 202 and 204 are to be utilized for forming a PMOS transistor and an NMOS transistor, respectively; the layers 232 and 238 can be identical and formed in the same processing step, and the layers 234 and 240 can be identical and formed in the same processing step. If layers 202 and 204 are to be utilized for forming a PMOS transistor and an NMOS transistor, respectfully; the layers 230 and 236 can be identical and formed in the same processing step, or the layers 230 and 236 can be different in comprising a different type of conductivity dopant relative to one another.